

# Extreme Ultraviolet Light Sources Supporting Next-Generation Lithography

Sam Gunnell EUV Product Manager

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#### **Overview**

#### Introduction

- What is Photolithography?
- Moore's Law
- Current State
- Why EUV?
- Key challenges
  - EUV Mask
  - EUV Photoresist
- EUV Sources for Research & Metrology
- Applications for EQ-10 Electrodeless Z-Pinch EUV Source



## What is Photolithography?

Photolithography is a process used in semiconductor device fabrication to pattern an integrated circuit onto a silicon wafer. It uses light to transfer a geometric pattern from a photomask to a photosensitive chemical photoresist on the substrate.

A series of chemical treatments then either etches the exposure pattern into the material or enables deposition of a new material in the desired pattern upon the material underneath the photoresist.





Source: Engadget, 2020





...States that transistor density of an integrated circuit doubles approximately every 24 months

...Represents an observation on the continuous improvement of production methods, particularly photolithography



#### **Resolution Enhancements Drive Moore's Law**

$$CD = k_1 \times \frac{\lambda}{NA}$$

CD ... critical dimension  $k_1$ ... process factor  $\lambda$  ... wavelength NA ... numerical aperture



### **Current state of Photolithography**



Source: Zeiss, 2020

- 193nm exposure wavelength
- ArF laser source
- Transmissive mask
- Transmissive projection optics



### **193nm Lithography at the Limit**

The current state of the art has reached its physical limits. The structures on a chip are now many times smaller than the wavelength of light used to make them, and any more progress will require a big change.





...Extreme Ultraviolet Lithography reduces the exposure wavelength from 193nm to 13.5nm, resulting in smaller critical dimensions in fewer process steps

$$\downarrow CD = k_1 \times \frac{\lambda}{NA}$$



## Lithography Timeline



Source: Zeiss, 2018



#### 14x Wavelength Reduction...

#### ...Introduces significant challenges

- Light-material interactions
- Defect control and metrology



#### **The EUV Scanner**



Source: ASML, Public, 2018



## Key Challenge: EUV Mask



Source: Engadget, 2020

- The EUV Mask is a patterned multilayer mirror
- The mask must be perfect to ensure defects are not transferred to the wafer, affecting yields
- Multiple inspection steps required throughout the manufacture and lifetime of the mask
- Only EUV inspection can "see" all defects



# **Key Challenge: EUV Photoresist**

- Photoacid Generation in EUV lithography is significantly different from DUV
- New chemistries required
- Candidate resists must be studied under EUV illumination before use in manufacturing



Source: AMOLF, 2018



#### **EUVL HVM Roadmap**

Requires access to EUV photons for fundamental research and metrology/inspection



#### Why not use the scanner source?



Source: ASML, 2018

- Massive footprint
- Driven by >20kW CO2 laser
- Prohibitively expensive to own and operate
- 250W EUV at intermediate focus
- Not suitable for research or metrology applications



#### **Alternative sources**

Researchers and toolmakers need reliable, cost-effective, accessible sources of EUV photons



#### **Synchrotron Radiation**

- Used for fundamental research, especially for resist patterning studies and metrology development
- Many examples of industry collaboration with government labs and academic institutions
- Limited number of synchrotron facilities
- Limited number of beamlines dedicated to EUV research topics



Source: Synchrotron Soleil, 2005



#### Laser Produced Plasma Sources (LPP)



Source: Bits & Chips, 2017

- Same concept as scanner source, but on smaller scale
- High brightness (~100W/mm^2 sr) required for high-throughput patterned mask inspection in the fab
- Complex debris mitigation strategies required
- High cost of ownership for materials research and certain mask inspection applications during mask manufacturing process



### **Discharge Produced Plasma Sources (DPP)**

# EUV-emitting Z-pinch generated by electrical discharge in a target gas (Typically Xenon)

Z-pinch: uses an electrical current in the plasma to generate a magnetic field that compresses it



Source: Everythingiselectric.com, 2015



#### **Electrode-based DPP**



- EUV generation in Xenon gas by high current discharge across electrodes
- Suitable for materials applications such as photoresist R&D
- Electrodes experience high current densities and are in direct contact with plasma
- Debris, stability, and spatial variation of the EUV emitting area are not suitable for metrology applications in production environments



### **EQ-10 Electrodeless Z-Pinch EUV™ Source**

- Unique inductive electrodeless DPP EUV source
- Pulse-to-pulse stability, spatial stability, and brightness suitable for certain metrology applications
- Ease of use and reliability suitable for photoresist R&D at Tier 1 semiconductor companies
- 13.5nm ±1% EUV Operation (Xenon)
  - Up to 20W into  $2\pi$  steradians
  - Brightness 8W/mm^2 sr
  - Source size <500um diameter FWHM
  - Frequency up to 2.5 kHz





### **Principle of Operation**



A HAMAMATSU Company

ENERGET

В

A

### **Typical Spectrum**



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1.2kHz 325V, 80mTorr Xe, corrected for Zr/polyimide filter, on-axis

## **EQ-10 in-band EUV Plasma Image**





A HAMAMATSU Company

### **Applications**

- Metrology
  - Actinic Mask Blank Inspection
  - Aerial Imaging for Patterned Mask Qualification
- Materials
  - Photoresist



#### **Actinic Mask Blank Inspection**

- Essential tool for EUV HVM infrastructure
- Enables high-sensitivity detection of printable defects inside Mo/Si multilayer

### **Aerial Imaging for Patterned Mask Qualification**

- EQ-10 allows emulation of scanner conditions for qualifying patterned masks
- Masks can be optimized and repaired before use in scanner



#### **Photoresist R&D Example**

- Customized beamline and wafer chamber
- Reliable source of EUV photons for photoresist exposure and outgassing studies
- Exposure times depend on beamline, optics and resist under study
- Example system:
  - 20 mJ resist exposure time of ~30 seconds
    - i.e. 40 mJ/min







## **Exposed Wafer**





### **Comparison of Alternative Sources**

	EQ-10 (electrodeless)	DPP (electrodes)	LPP	
Brightness	$\checkmark$	$\checkmark$	$\checkmark \checkmark \checkmark$	
Cleanliness	$\checkmark\checkmark$	$\checkmark$	$\checkmark$	
Stability	$\checkmark\checkmark$	$\checkmark$	$\checkmark\checkmark$	
Reliability	$\checkmark \checkmark \checkmark$	$\checkmark \checkmark$	$\checkmark \checkmark \checkmark$	
Cost	\$\$\$	\$\$	\$\$\$\$	
Applications	Mask Blank Inspection Patterned Mask Qualification Materials R&D	Metrology Research Materials R&D	Patterned Mask Inspection	



### Summary

- EUV Lithography has entered high volume manufacturing for certain layers, but 193nm multi-patterning is still the primary production method
- Researchers and metrologists continue to need cost-effective sources of EUV photons to address EUV HVM roadmap and infrastructure requirements
- Each type of EUV source has its own advantages and disadvantages: there is no one-sizefits all solution
- The market for alternative EUV light sources is small, but rich with unique and highly differentiated technologies
- The Energetiq EQ-10 Electrodeless Z-Pinch EUV Source is a reliable and stable source of photons for EUV metrology and infrastructure development
- >30 systems sold and large installed base with consistent operation over 15 years



### Thank you!

And please feel free to reach out with further questions

#### **Contact Information:**

Sam Gunnell EUV Product Manager sgunnell@energetiq.com



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1 Weeks Break						
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# Thank you

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